



- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Advanced high cell density Trench technology

## Product Summary



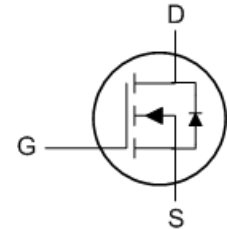
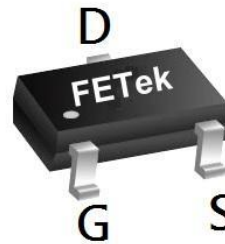
BVDSS	RDSON	ID
60V	85mΩ	3A

## Description

The FKUC6002 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in Power management applications.

The FKUC6002 meet the RoHS and Green Product requirement, with full function reliability approved.

## SOT23S Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	±20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	3	A
$I_D@T_A=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	2	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	12	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sup>3</sup>	1.25	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	125	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup> ( $t \leq 10s$ )	---	100	°C/W

Electrical Characteristics ( $T_J=25\text{ }^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=3.5A$	---	65	85	m $\Omega$
		$V_{GS}=4.5V, I_D=3A$	---	75	100	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.7	2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=48V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=5V, I_D=5A$	---	7	---	S
$Q_g$	Total Gate Charge (10V)	$V_{DS}=12V, V_{GS}=10V, I_D=5A$	---	5.5	---	nC
$Q_{gs}$	Gate-Source Charge		---	1.8	---	
$Q_{gd}$	Gate-Drain Charge		---	2.4	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=12V, V_{GS}=10V, R_G=3.3\Omega, I_D=5A$	---	6	---	ns
$T_r$	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
$T_f$	Fall Time		---	7	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	695	---	pF
$C_{oss}$	Output Capacitance		---	148	---	
$C_{rss}$	Reverse Transfer Capacitance		---	7	---	

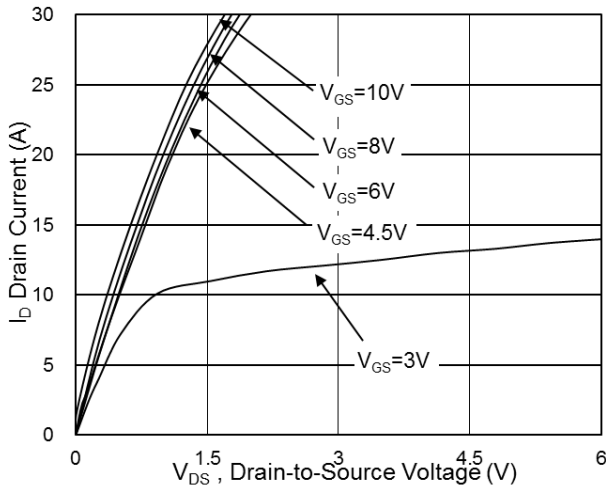
## Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V$ , Force Current	---	---	3	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V

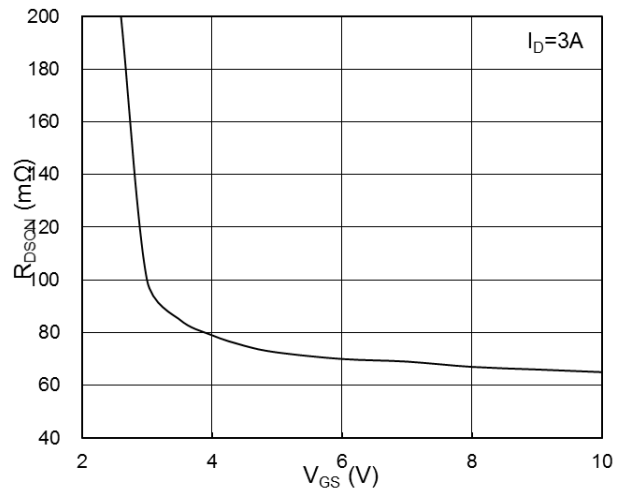
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by 150 $^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

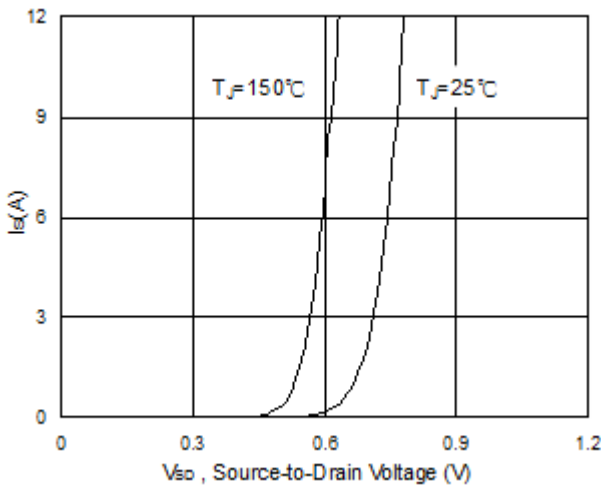
### Typical Characteristics



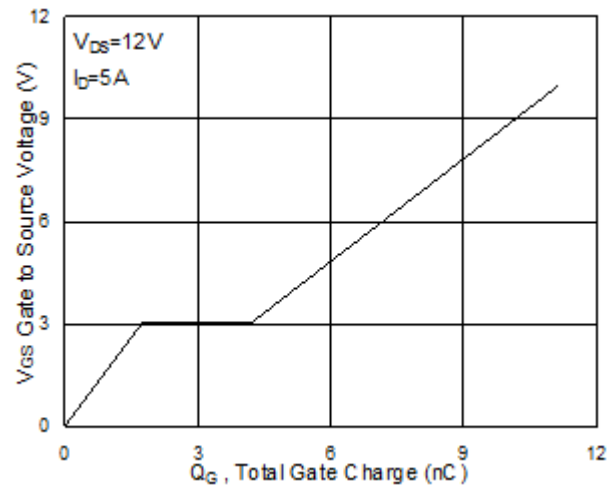
**Fig.1 Typical Output Characteristics**



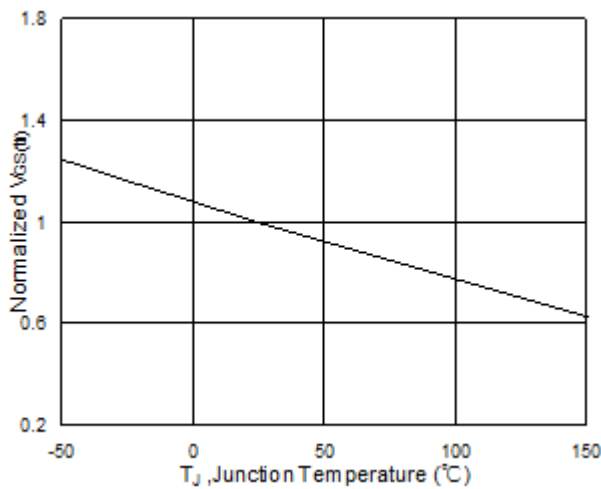
**Fig.2 On-Resistance vs G-S Voltage**



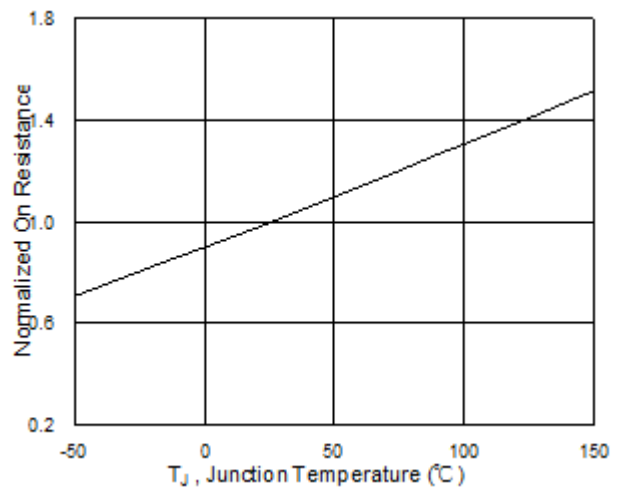
**Fig.3 Source Drain Forward Characteristics**



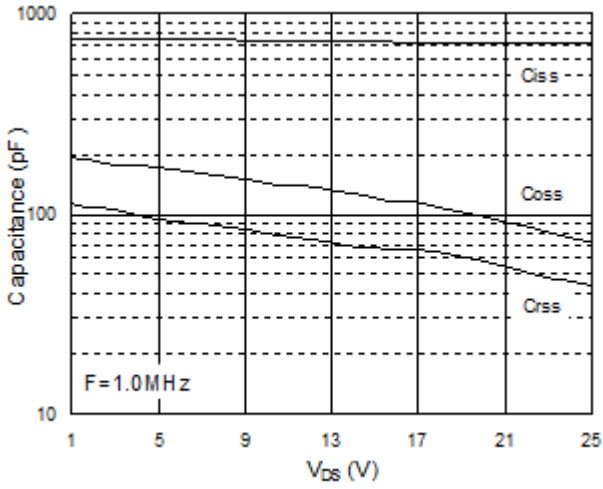
**Fig.4 Gate-Charge Characteristics**



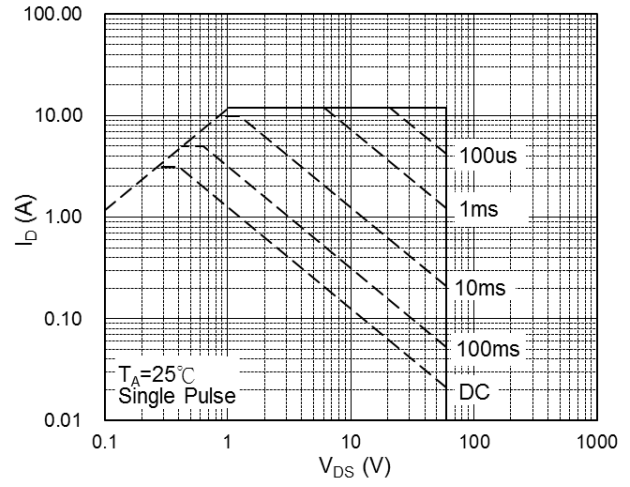
**Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$**



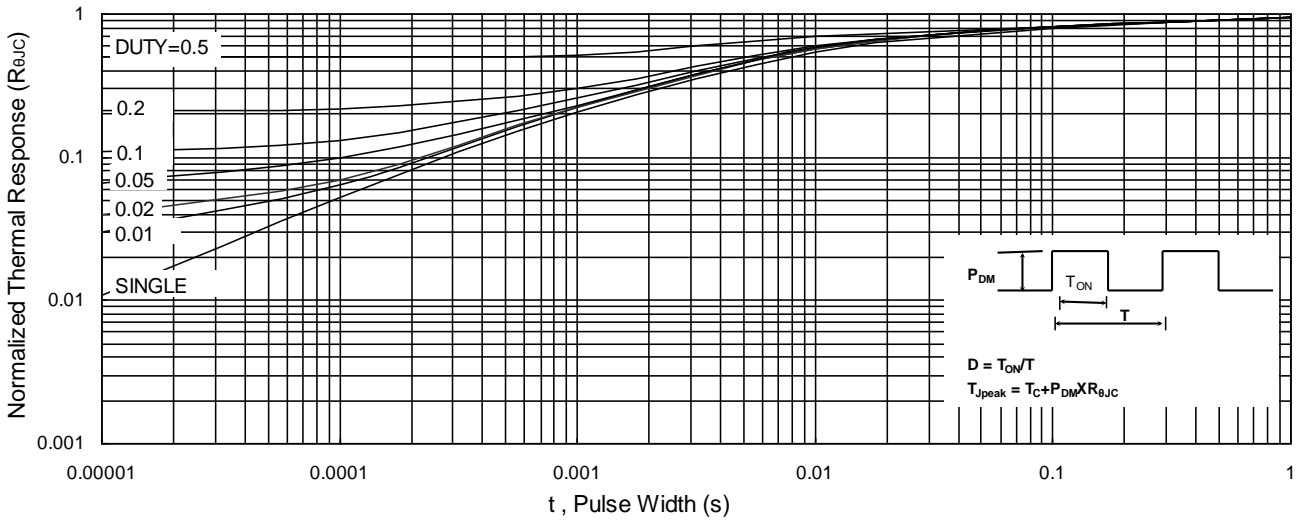
**Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$**



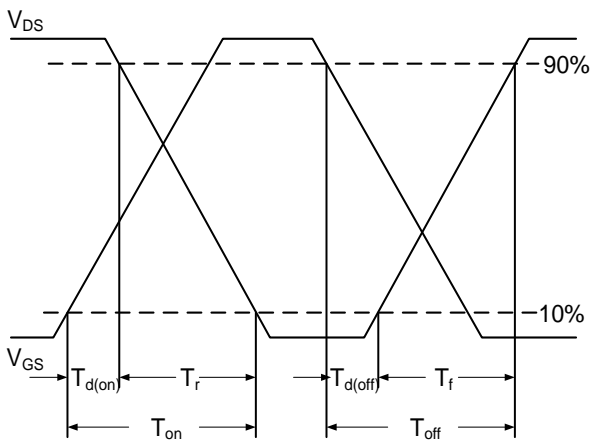
**Fig.7 Capacitance**



**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**